

# TK60D08J1

## Switching Regulator Application

- High-Speed switching
- Small gate charge:  $Q_g = 86 \text{ nC}$  (typ.)
- Low drain-source ON resistance:  $R_{DS(ON)} = 6.2 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 120 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 75 \text{ V}$ )
- Enhancement-mode:  $V_{th} = 1.1 \text{ to } 2.3 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Characteristics                                      |                | Symbol    | Rating     | Unit             |
|--|----------------|-----------|------------|------------------|
| Drain-source voltage                                 |                | $V_{DSS}$ | 75         | V                |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |                | $V_{DGR}$ | 75         | V                |
| Gate-source voltage                                  |                | $V_{GSS}$ | $\pm 20$   | V                |
| Drain current  | DC (Note 1)    | $I_D$     | 60         | A                |
|  | Pulse (Note 1) | $I_{DP}$  | 240        |                  |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) |                | $P_D$     | 140        | W                |
| Single pulse avalanche energy (Note 2)               |                | $E_{AS}$  | 498        | mJ               |
| Avalanche current                                    |                | $I_{AR}$  | 60         | A                |
| Repetitive avalanche energy (Note 3)                 |                | $E_{AR}$  | 9.2        | mJ               |
| Channel temperature                                  |                | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature range                            |                | $T_{stg}$ | -55 to 150 | $^\circ\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

| Characteristics                        | Symbol         | Max  | Unit                      |
|--|----------------|------|---------------------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 0.89 | $^\circ\text{C}/\text{W}$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 83.3 | $^\circ\text{C}/\text{W}$ |

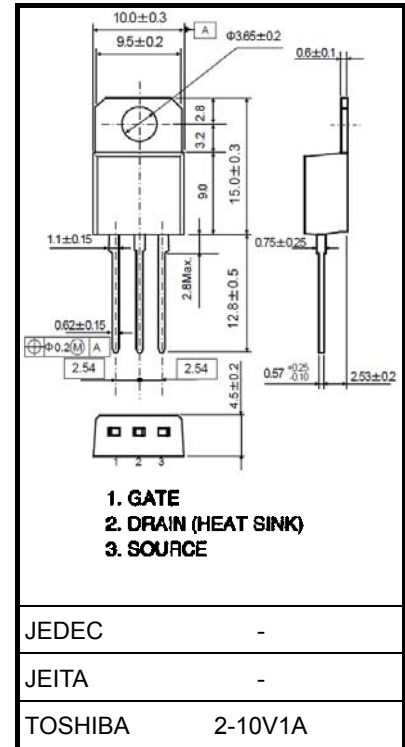
Note 1: Ensure that the channel & lead temperature does not exceed  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = 25 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$ ,  $L = 200 \text{ }\mu\text{H}$ ,  $I_{AR} = 60 \text{ A}$ ,  $R_G = 1 \Omega$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

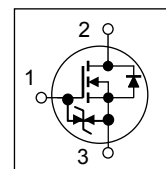
This transistor is an electrostatic sensitive device. Handle with care.

Unit: mm



Weight: 1.35 g (typ.)

## Internal Connection



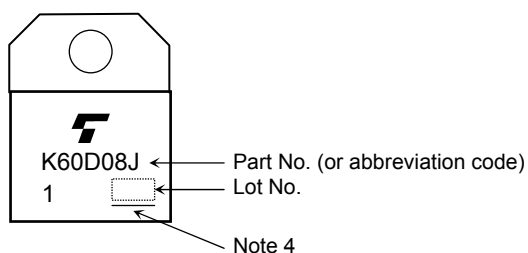
## Electrical Characteristics (Ta = 25°C)

| Characteristics                                 |               | Symbol        | Test Condition   | Min | Typ. | Max      | Unit             |
|---|---------------|---------------|--|-----|------|----------|------------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$  | —   | —    | $\pm 10$ | $\mu\text{A}$    |
| Drain cut-OFF current                           |               | $I_{DSS}$     | $V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}$  | —   | —    | 10       | $\mu\text{A}$    |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$  | 75  | —    | —        | V                |
|   |               | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$  | 60  | —    | —        |                  |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$  | 1.1 | —    | 2.3      | V                |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$   | —   | 7.1  | 9.3      | $\text{m}\Omega$ |
|   |               |               | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$  | —   | 6.2  | 7.8      |                  |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 30\text{ A}$  | 60  | 120  | —        | S                |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$  | —   | 5450 | —        | pF               |
| Reverse transfer capacitance                    |               | $C_{rss}$     |  | —   | 320  | —        |                  |
| Output capacitance                              |               | $C_{oss}$     |  | —   | 1260 | —        |                  |
| Switching time                                  | Rise time     | $t_r$         | <p><math>V_{GS} = 10\text{ V}, 0\text{ V}</math><br/> <math>I_D = 30\text{ A}</math><br/> <math>R_L = 1\ \Omega</math><br/> <math>V_{DD} \approx 30\text{ V}</math><br/> <math>4.7\ \Omega</math><br/> <math>V_{OUT}</math><br/> <math>Duty \leq 1\%, t_w = 10\ \mu\text{s}</math></p> | —   | 5    | —        | ns               |
|   | Turn-ON time  | $t_{on}$      |  | —   | 20   | —        |                  |
|   | Fall time     | $t_f$         |  | —   | 15   | —        |                  |
|   | Turn-OFF time | $t_{off}$     |  | —   | 96   | —        |                  |
| Total gate charge (gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 60\text{ V}, V_{GS} = 5\text{ V}, I_D = 60\text{ A}$   | —   | 48   | —        | nC               |
|   |               |               | $V_{DD} \approx 60\text{ V}, V_{GS} = 10\text{ V}, I_D = 60\text{ A}$  | —   | 86   | —        |                  |
| Gate-source charge 1                            |               | $Q_{gs1}$     | $V_{DD} \approx 60\text{ V}, V_{GS} = 10\text{ V}, I_D = 60\text{ A}$  | —   | 16   | —        |                  |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |  | —   | 20   | —        |                  |
| Gate switch charge                              |               | $Q_{SW}$      |  | —   | 27   | —        |                  |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol    | Test Condition                               | Min | Typ. | Max  | Unit |
|---|-----------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —  | —   | —    | 60   | A    |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —  | —   | —    | 240  | A    |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 60\text{ A}, V_{GS} = 0\text{ V}$  | —   | -0.9 | -1.2 | V    |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 60\text{ A}, V_{GS} = 0\text{ V},$ | —   | 63   | —    | ns   |
| Reverse recovery charge                   | $Q_{rr}$  | $dI_{DR}/dt = 50\text{ A}/\mu\text{s}$       | —   | 63   | —    | nC   |

## Marking

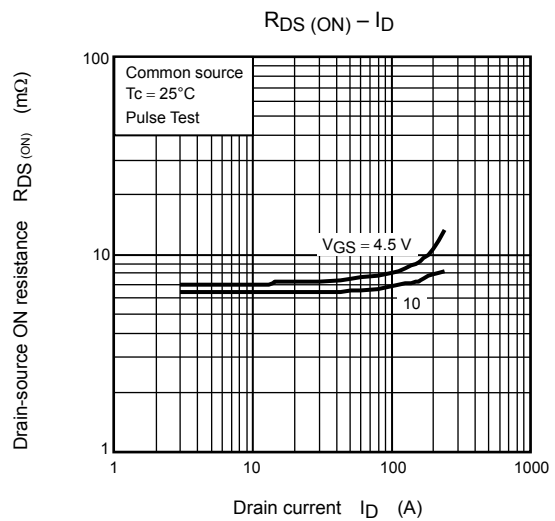
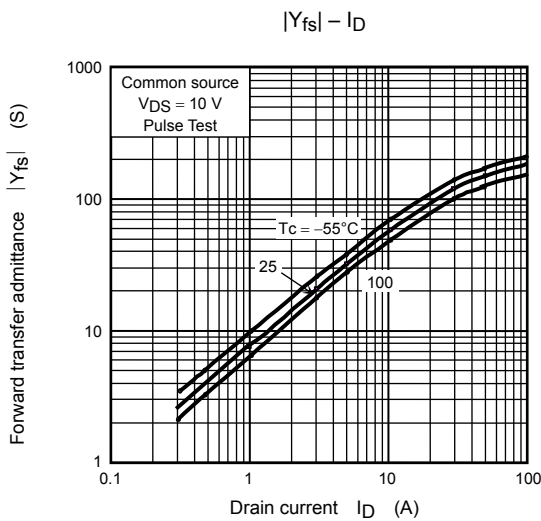
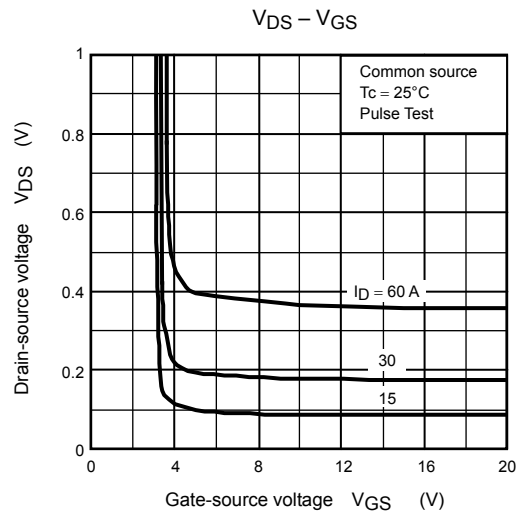
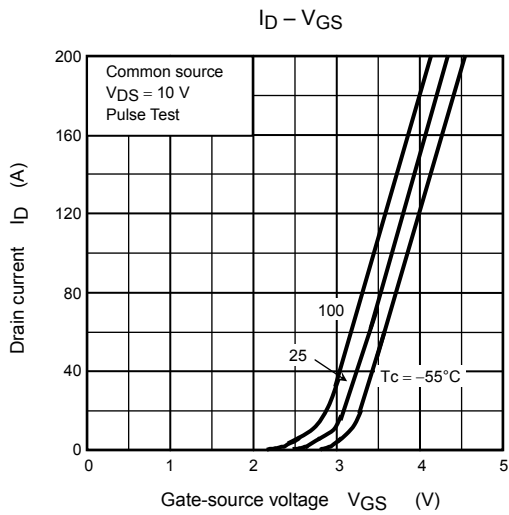
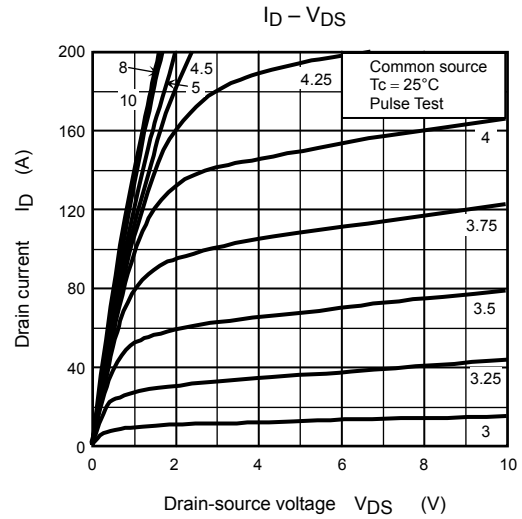
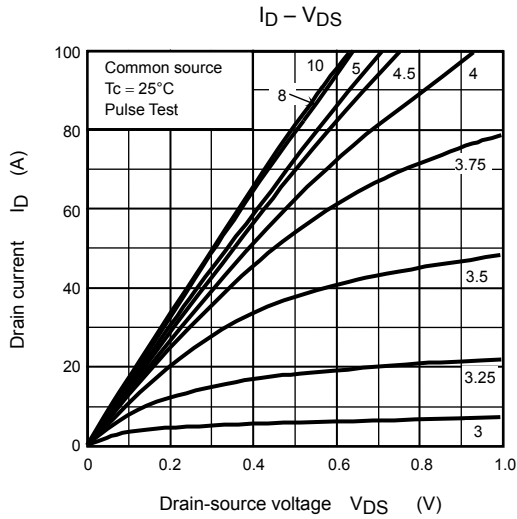


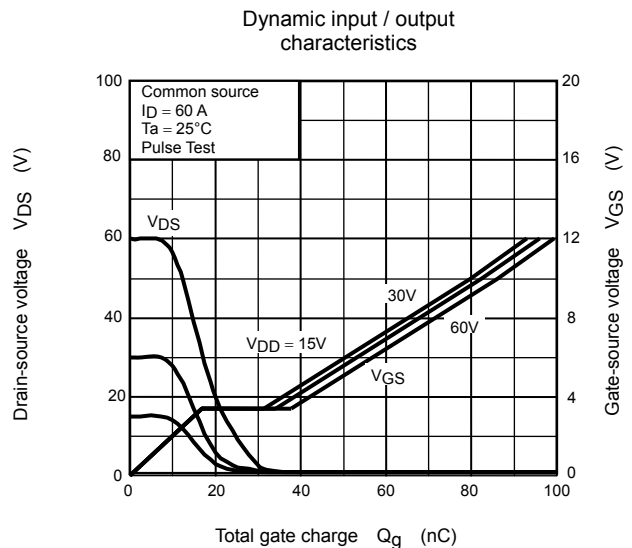
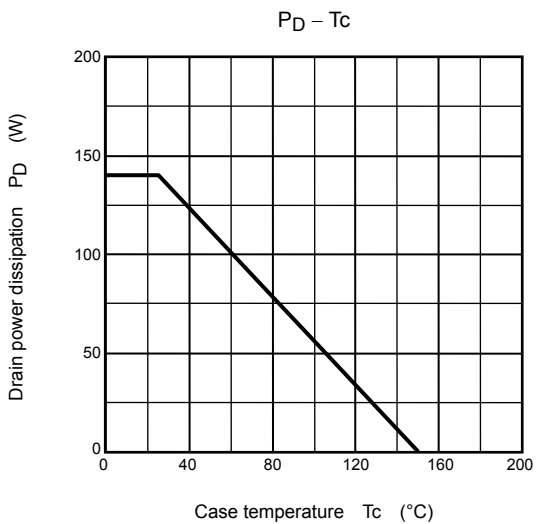
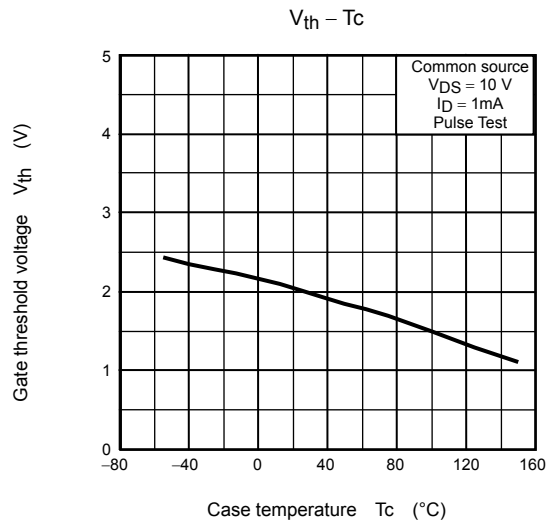
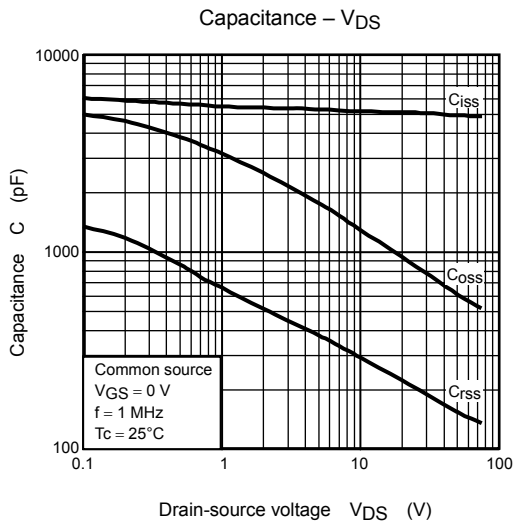
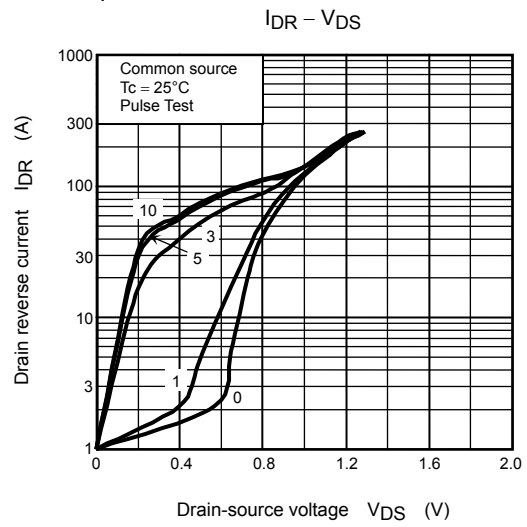
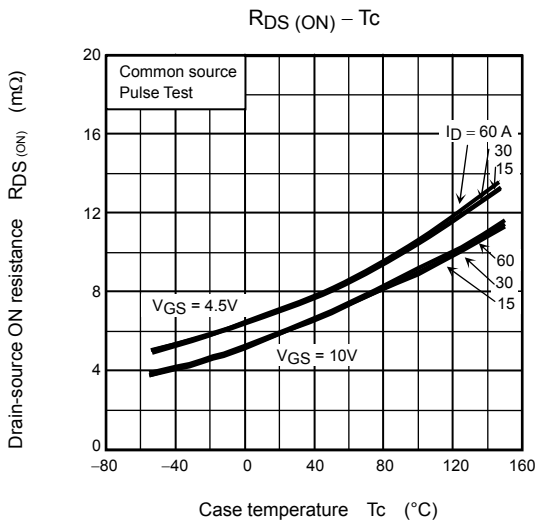
Note 4: A line under a Lot No. identifies the indication of product Labels.

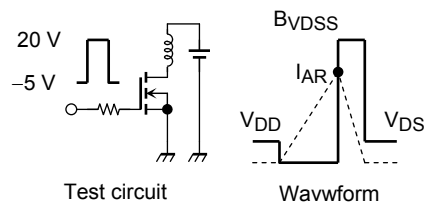
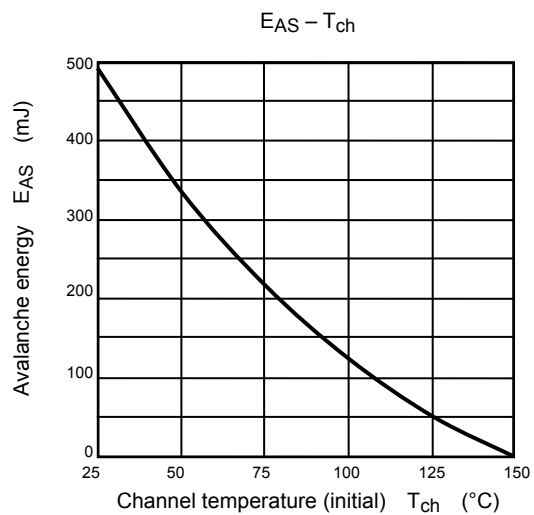
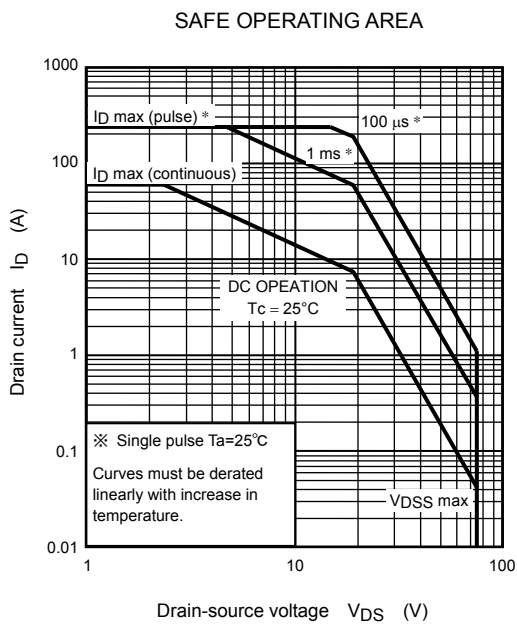
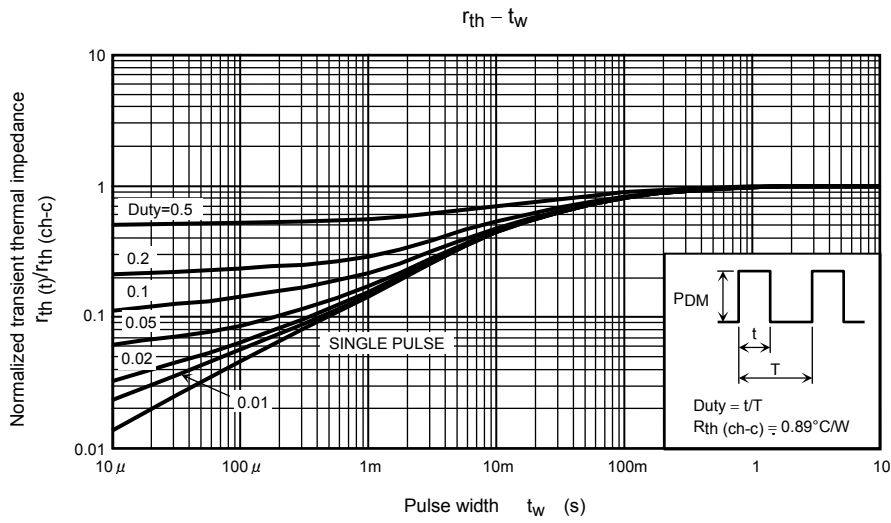
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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$R_G = 1\ \Omega$   
 $V_{DD} = 25\ V, L = 200\ \mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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